

[Abstract]

A semiconductor device of the embodiment includes a stacked body, a first insulating layer, first and second staircase portions 2, and a second insulating layer 46. The stacked body
5 includes a first electrode layer 41 (WLDD) and a second electrode layer 41 (SGD). The first and second staircase portions 2 are provided in a first end portion 101 a second end region 102. The second insulating layer 46 extends in the X-direction. The second insulating layer divides the second
10 electrode layer 41 (SGD) in the X-direction direction. A length L1 in the X-direction of the second insulating layer 46 is longer than a length L2 in the x-direction of the second electrode layer 41 (SGD) and shorter than a length L3 in the X-direction of the first electrode layer 41 (WLDD).